



ALD/CVD High K and Metal Precursors

For the Semiconductor IC Market

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TABLE OF CONTENTS

EXECUTIVE SUMMARY	6
1 SCOPE	10
2 IC TECHNOLOGY ROADMAP AND IMPLICATIONS	10
2.1 Logic Transistor Evolution.....	11
2.2 Metallization Evolution.....	13
2.2.1 More than Moore Stacked Packaging	15
2.3 Memory Evolution	16
2.4 Implication of Device Evolution to IC Fabs, Processes and Materials	17
2.5 Looking Beyond 2019.....	21
2.5.1 Moving from 300mm to 450mm Wafers	26
2.6 Forecast of Wafer Starts by Nodes and Product Mixes by Year	29
3 HIGH K GATE DIELECTRICS	30
3.1 Application Description and Current Gate Materials	31
3.2 Front End of Line Organometallic Precursor Overview (Gate and Capacitors)..	35
3.3 Future Gate Dielectrics and Requirements.....	36
3.4 Future Gate Material Candidates and Precursors.....	38
3.5 Hi K Gate Dielectric Market and Forecast	40
4 HIGH-K CAPACITORS FOR MEMORY DEVICES.....	41
4.1 High K Current Capacitor materials and precursors	43
4.2 Future Capacitor Materials and Precursors.....	45
4.3 High K Capacitor Market and Forecast	46
5 INTERCONNECT	48
5.1 Interconnect Trends.....	49
5.2 Metal Plugs and Interconnect Materials CVD/ALD Metals Forecast	54
5.3 Alternative Barrier, Interconnect and Capping Materials	55
5.3.1 Chemical Vapor Deposited Aluminum.....	57
5.3.2 Atomic Layer Deposition Development for Barrier Films.....	57
5.3.3 Copper Cap after CMP	58
6 PRECURSOR DELIVERY	59
7 ORGANOMETALLIC PRECURSORS TOTAL MARKET SUMMARY AND MARKET DYNAMICS.....	60
7.1 Supply Value Chain	62
7.2 Market Shares	64
7.2.1 Regional Supplier Ranking	64
7.3 FUSI	67
7.3.1 Advantages of FUSI.....	68
7.3.2 FUSI Challenges.....	69
7.4 High-κ Dielectric and Metal-Gate Technology.....	69

7.5 Advantages of Metal Gate (vs. Polysilicon Gate).....	70
7.5.1 Metal-Gate Challenges.....	70
7.5.2 High-κ Metal-Gate Process Flow Notes:.....	73

Appendix

Appendix A: FUSI, Gate First, Gate Last Process Technologies.....	66
Appendix B: Chemical Structure of the Complexes TDMAT and TDEAT	76

List of Figures

Figure 1: Comparison of Planar and 3D (TriGate/FinFET) CMOS Transistor. (A) Planar, (B) FinFET on Bulk Si & (C) FinFET SOI.....	11
Figure 2: One Version of InGaAs on Si wafer.....	12
Figure 3: MPU / MCU Device Roadmap May 2014.....	13
Figure 4: Non-Volatile Memory Device Roadmap May 2014	16
Figure 5. 22nm FinFET Metal Gate Electrode Materials (ref. Chipworks ASMC 2014) ...	19
Figure 6: Time Line Logic Device Technology through 2020	22
Figure 7: Forecast Silicon Shipment Trends by Node and Product Type (thousands of 200mm equivalent wafers/year).....	30
Figure 8: CMOS with SiO ₂ Gate Dielectric Structure.....	33
Figure 9: Device with Gate First High-κ Gate Dielectric Structure	33
Figure 10: High-K Gate Dielectric & Metal Electrode Precursor Forecast (Logic & DRAM)	40
Figure 11: DRAM Vertical Stacked Capacitor Application.....	42
Figure 12: 32nm and beyond Vertical Capacitor.....	43
Figure 13: High-κ Precursors for Capacitor (Memory).....	46

Figure 14: High-κ and ALD Applications	49
Figure 15: Revenue Forecast for CVD (or ALD) Plug Metal (Metal 0), Barrier Precursors and Seeds	55
Figure 16: CVD/ALD High-κ Materials Market, assumes Co as Barrier for ≤ 14nm.....	61
Figure 17: Hi K / ALD Precursor Supplier Market Share (% of WW Revenues).....	64
Figure A1: Device with Gate-First.....	66
Figure A2: Device with Replacement-Metal Gate-Last.....	67
Figure A3: SEM of FUSI Device	67
Figure A4: FUSI Process Flow	68
Figure A5: One Possible Metal-Gate-First Process Flow.....	72
Figure A6: Intel Penryn’s Replacement-Metal-Gate Process	74

List of Tables

Table 1: Front End of Line High k and Metal CVD/ALD Precursor Revenues Forecast ...	6
Table 2: Front End Dielectric Materials & Processes, 2014, 2016 & 2018	7
Table 3: Leading Edge Interconnect Materials & Processes, 2014, 2016 and 2018.....	8
Table 4: Emerging Memory Device Research and Associated Challenges – ITRS.....	24
Table 5: Emerging Development on Logic Devices – ITRS (source: International Technology Roadmap for Semiconductor, www.itrs.net).....	25
Table 6: Dielectric Constant of Transistor Gate and Memory Capacitor Dielectric Material.....	34
Table 7: 2013 ITRS Interconnect Difficult Challenges.....	52
Table 8: Materials & Process Options for 2014, 2016 & 2018.....	53
Table 9: Organometallic Precursors: Synthesizers and Suppliers to the IC Market.....	63